



4-/6-/8-Channel, $\pm 30\text{kV}$ ESD Protectors in μDFN

General Description

The MAX13204E/MAX13206E/MAX13208E low-capacitance $\pm 30\text{kV}$ ESD-protection diode arrays are designed to protect sensitive electronics attached to communication lines. Each channel consists of a pair of diodes that steer ESD current pulses to V_{CC} or GND.

The MAX13204E/MAX13206E/MAX13208E protect against ESD pulses up to $\pm 15\text{kV}$ Human Body Model (HBM), $\pm 14\text{kV}$ Contact Discharge, and $\pm 30\text{kV}$ Air-Gap Discharge, as specified in IEC 61000-4-2. These devices have a 6pF on-capacitance per channel, making them ideal for use on high-speed data I/O interfaces.

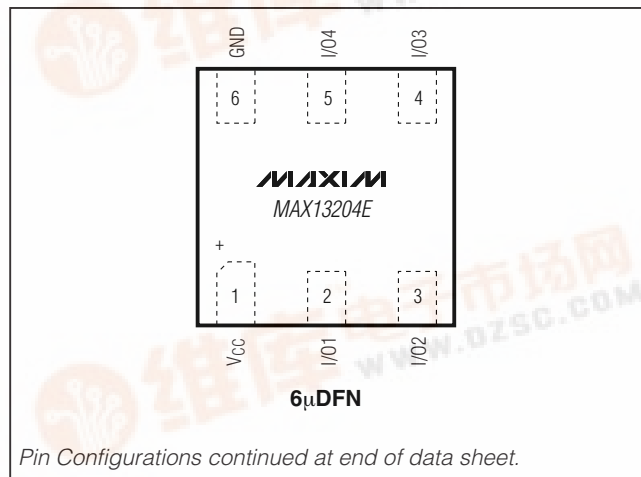
The MAX13204E is a quad-ESD structure designed for Ethernet and FireWire™ applications. The MAX13206E/MAX13208E are 6-channel and 8-channel devices. They are designed for cell-phone connectors and SVGA video connections.

These devices are available in 6-, 8-, and 10-pin μDFN packages and are specified over the -40°C to $+125^\circ\text{C}$ automotive operating temperature range.

Applications

USB	Ethernet
USB 2.0	Video
PDAs	Cell Phones
FireWire	

Pin Configurations



Features

- ◆ High-Speed Data Line ESD Protection
 - $\pm 15\text{kV}$ —Human Body Model
 - $\pm 14\text{kV}$ —IEC 61000-4-2, Contact Discharge
 - $\pm 30\text{kV}$ —IEC 61000-4-2, Air-Gap Discharge
- ◆ Tiny μDFN Package
- ◆ Low 6pF Input Capacitance
- ◆ Low 1nA (Max) Leakage Current
- ◆ $+0.9\text{V}$ to $+16\text{V}$ Supply Voltage Range

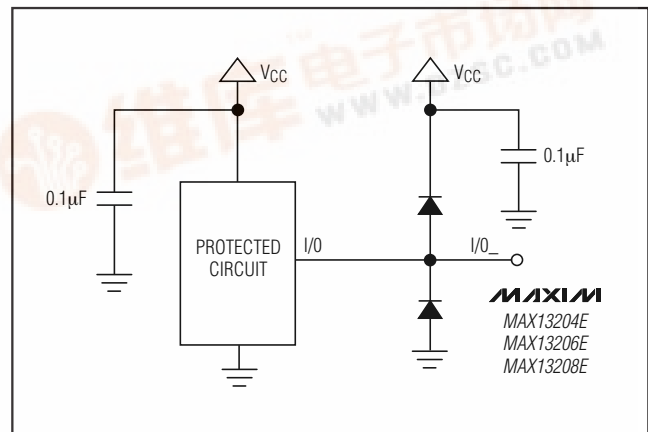
Ordering Information

PART*	PIN-PKG	PROTECTED I/O PORTS	TOP MARK	PKG CODE
MAX13204EALT+	6 μDFN	4	AAO	L622-1
MAX13206EALA+	8 μDFN	6	AAL	L822-1
MAX13208EALB+	10 μDFN	8	AAD	L1022-1

*All devices operate under the -40°C to $+125^\circ\text{C}$ automotive temperature range.

+Denotes lead-free package

Typical Operating Circuit



FireWire is a trademark of Apple Computer, Inc.

μDFN is a trademark of Maxim Integrated Products, Inc.

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ABSOLUTE MAXIMUM RATINGS

V_{CC} to GND -0.3V to +18V
 I/O_{-} to GND -0.3V to ($V_{CC} + 0.3\text{V}$)
 Continuous Power Dissipation ($T_A = +70^\circ\text{C}$)
 6-Pin, 2mm x 2mm μDFN (derate 4.5mW/ $^\circ\text{C}$
 above $+70^\circ\text{C}$) 358mW
 8-Pin, 2mm x 2mm μDFN (derate 4.8mW/ $^\circ\text{C}$
 above $+70^\circ\text{C}$) 381mW
 10-Pin, 2mm x 2mm μDFN (derate 5.0mW/ $^\circ\text{C}$
 above $+70^\circ\text{C}$) 403mW

Operating Temperature Range -40°C to $+125^\circ\text{C}$
 Storage Temperature Range -65°C to $+150^\circ\text{C}$
 Junction Temperature $+150^\circ\text{C}$
 Lead Temperature (soldering, 10s) $+300^\circ\text{C}$

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

ELECTRICAL CHARACTERISTICS

($V_{CC} = +5\text{V} \pm 5\%$, $T_A = T_{MIN}$ to T_{MAX} , unless otherwise noted. Typical values are at $V_{CC} = +5\text{V}$ and $T_A = +25^\circ\text{C}$.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Supply Voltage	V_{CC}		0.9		16.0	V
Supply Current	I_{CC}			1	100	nA
Diode Forward Voltage	V_F	$I_F = 10\text{mA}$	0.65		0.95	V
Channel Clamp Voltage (Note 2)	V_C	$T_A = +25^\circ\text{C}$, $\pm 15\text{kV}$ Human Body Model, $I_F = 10\text{A}$	Positive transients		$V_{CC} + 25$	V
			Negative transients		-25	
		$T_A = +25^\circ\text{C}$, $\pm 14\text{kV}$ Contact Discharge (IEC 61000-4-2), $I_F = 42\text{A}$	Positive transients		$V_{CC} + 80$	
			Negative transients		-80	
		$T_A = +25^\circ\text{C}$, $\pm 30\text{kV}$ Air-Gap Discharge (IEC 61000-4-2), $I_F = 90\text{A}$	Positive transients		$V_{CC} + 120$	
			Negative transients		-120	
Channel Leakage Current (Note 3)		$T_A = -40^\circ\text{C}$ to $+50^\circ\text{C}$	-1		+1	nA
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	-1		+1	μA
Channel Input Capacitance		$V_{CC} = 5\text{V}$, bias of $V_{CC}/2$, $f = 1\text{MHz}$ (Note 3)		6	7	pF
ESD PROTECTION						
Human Body Model				± 15		kV
IEC 61000-4-2 Contact Discharge				± 14		kV
IEC 61000-4-2 Air-Gap Discharge				± 30		kV

Note 1: Limits over temperature are guaranteed by design, not production tested.

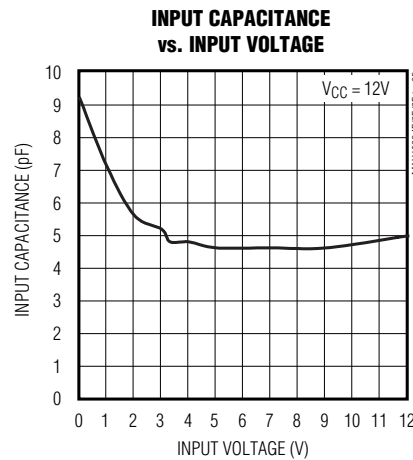
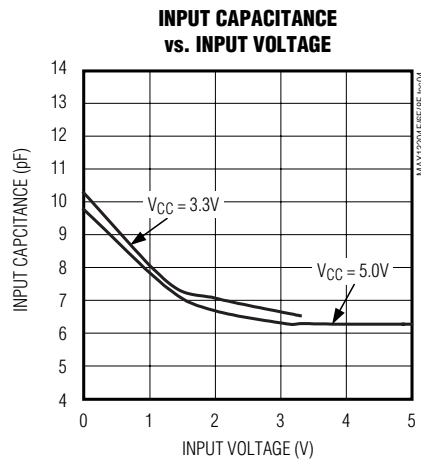
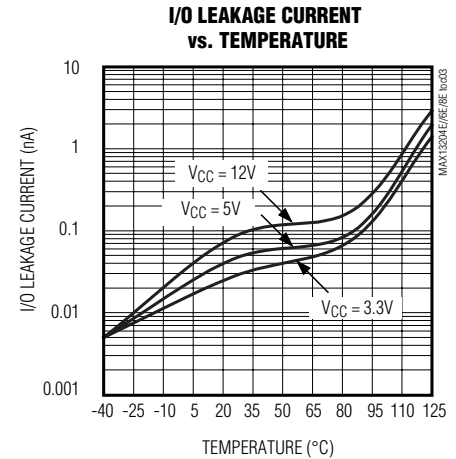
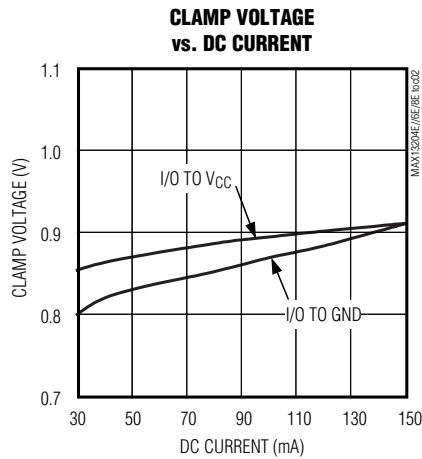
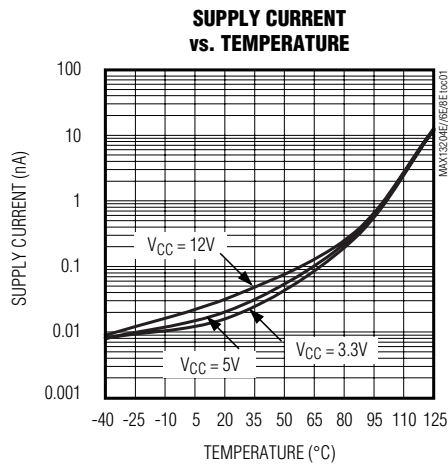
Note 2: Idealized clamp voltages ($L1 = L2 = L3 = 0$) (Figure 1); see the *Applications Information* section for more information.

Note 3: Guaranteed by design. Not production tested.

4-/6-/8-Channel, $\pm 30\text{kV}$ ESD Protectors in μDFN

Typical Operating Characteristics

($V_{CC} = +5\text{V}$, $T_A = +25^\circ\text{C}$, unless otherwise noted.)



Pin Description

PIN			NAME	FUNCTION
MAX13204E	MAX13206E	MAX13208E		
1	1	1	V_{CC}	Power-Supply Input. Bypass V_{CC} to GND with a $0.1\mu\text{F}$ ceramic capacitor. Place the capacitor as close as possible to the device.
—	—	—	N.C.	No Connection. Not internally connected.
2–5	2–7	2–9	I/O ₋	ESD-Protected Channel
6	8	10	GND	Ground

4-/6-/8-Channel, $\pm 30\text{kV}$ ESD Protectors in μDFN

Detailed Description

The MAX13204E/MAX13206E/MAX13208E are diode arrays designed to protect sensitive electronics against damage resulting from ESD conditions or transient voltages. The low input capacitance makes these devices ideal for high-speed data lines. The MAX13204E/MAX13206E/MAX13208E protect four, six, and eight channels, respectively.

The MAX13204E/MAX13206E/MAX13208E are designed to work in conjunction with a device's intrinsic ESD protection. The MAX13204E/MAX13206E/MAX13208E limit the excursion of the ESD event to below $\pm 25\text{V}$ peak voltage when subjected to the Human Body Model waveform. When subjected to the IEC 61000-4-2 waveform, the peak voltage is limited to $\pm 80\text{V}$ when subjected to Contact Discharge and $\pm 120\text{V}$ when subjected to Air-Gap Discharge. The device that is being protected by the MAX13204E/MAX13206E/MAX13208E must be able to withstand these peak voltages plus any additional voltage generated by the parasitic board.

Applications Information

Design Considerations

Maximum protection against ESD damage results from proper board layout (see the *Layout Recommendations* section and Figure 2). A good layout reduces the parasitic series inductance on the ground line, supply line, and protected signal lines.

The MAX13204E/MAX13206E/MAX13208E ESD diodes clamp the voltage on the protected lines during an ESD event and shunt the current to GND or V_{CC} . In an ideal circuit, the clamping voltage, V_C , is defined as the forward voltage drop, V_F , of the protection diode plus any supply voltage present on the cathode.

For positive ESD pulses:

$$V_C = V_{CC} + V_F$$

For negative ESD pulses:

$$V_C = -V_F$$

In reality, the effect of the parasitic series inductance on the lines must also be considered (Figure 1).

For positive ESD pulses:

$$V_C = V_{CC} + V_F(D1) + \left(L1 \times \frac{d(I_{ESD})}{dt} \right) + \left(L2 \times \frac{d(I_{ESD})}{dt} \right)$$

For negative ESD pulses:

$$V_C = - \left(V_F(D2) + \left(L1 \times \frac{d(I_{ESD})}{dt} \right) + \left(L3 \times \frac{d(I_{ESD})}{dt} \right) \right)$$

where I_{ESD} is the ESD current pulse.

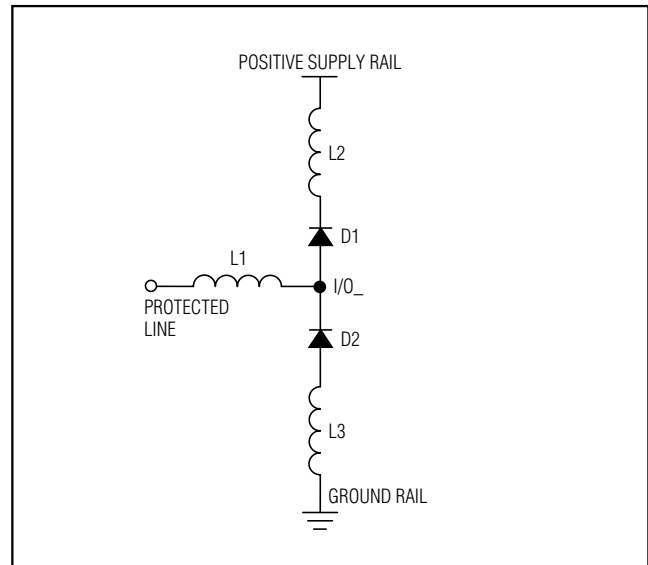


Figure 1. Parasitic Series Inductance

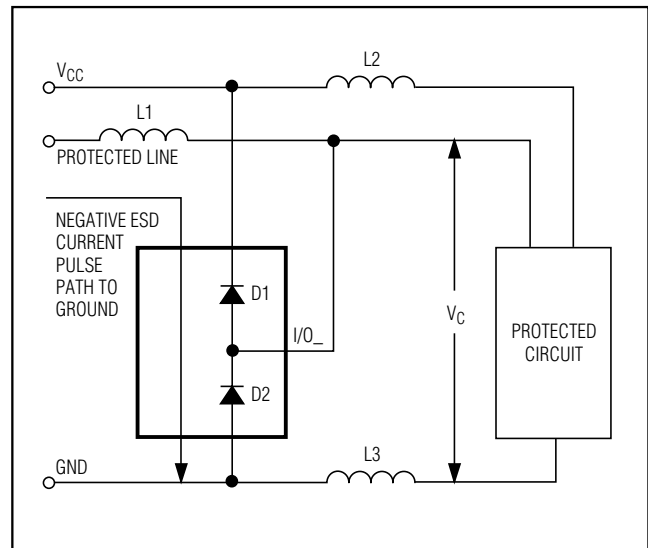


Figure 2. Layout Considerations

4-/6-/8-Channel, $\pm 30\text{kV}$ ESD Protectors in μDFN

During an ESD event, the current pulse rises from zero to peak value in nanoseconds (Figure 3). For example, in a 15kV IEC-61000-4-2 Air-Gap Discharge ESD event, the pulse current rises to approximately 45A in 1ns ($di/dt = 45 \times 10^9$). An inductance of only 10nH adds an additional 450V to the clamp voltage. An inductance of 10nH represents approximately 0.5in of board trace. Regardless of the device's specified diode clamp voltage, a poor layout with parasitic inductance significantly increases the effective clamp voltage at the protected signal line.

A low-ESR 0.1 μF capacitor must be used between V_{CC} and GND. This bypass capacitor absorbs the charge transferred by a +14kV IEC-61000-4-2 Contact Discharge ESD event.

Ideally, the supply rail (V_{CC}) would absorb the charge caused by a positive ESD strike without changing its regulated value. In reality, all power supplies have an effective output impedance on their positive rails. If a power supply's effective output impedance is 1Ω , then by using $V = I \times R$, the clamping voltage of V_C increases by the equation $V_C = I_{ESD} \times R_{OUT}$. An +8kV IEC 61000-4-2 ESD event generates a current spike of 24A, so the clamping voltage increases by $V_C = 24\text{A} \times 1\Omega$, or $V_C = 24\text{V}$. Again, a poor layout without proper bypassing increases the clamping voltage. A ceramic chip capacitor mounted as close to the MAX13204E/MAX13206E/MAX13208E V_{CC} pin is the best choice for this application. A bypass capacitor should also be placed as close to the protected device as possible.

$\pm 30\text{kV}$ ESD Protection

ESD protection can be tested in various ways. The MAX13204E/MAX13206E/MAX13208E are characterized for protection to the following limits:

- $\pm 15\text{kV}$ using the Human Body Model
- $\pm 14\text{kV}$ using the Contact Discharge method specified in IEC 61000-4-2
- $\pm 30\text{kV}$ using the IEC 61000-4-2 Air-Gap Discharge method

ESD Test Conditions

ESD performance depends on a number of conditions. Contact Maxim for a reliability report that documents test setup, methodology, and results.

Human Body Model

Figure 4 shows the Human Body Model, and Figure 5 shows the current waveform it generates when discharged into a low impedance. This model consists of a 100pF capacitor charged to the ESD voltage of interest, which is then discharged into the device through a $1.5\text{k}\Omega$ resistor.

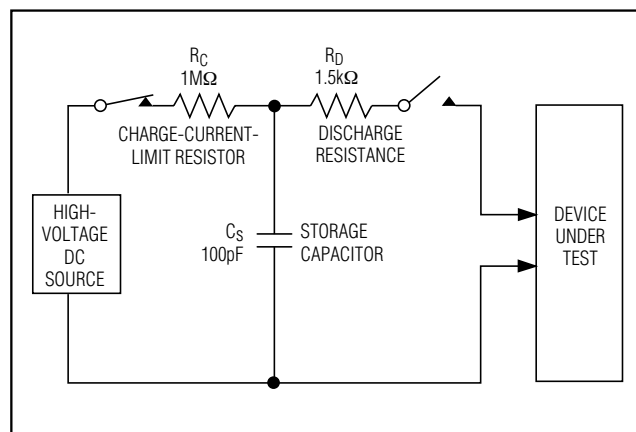


Figure 4. Human Body ESD Test Model

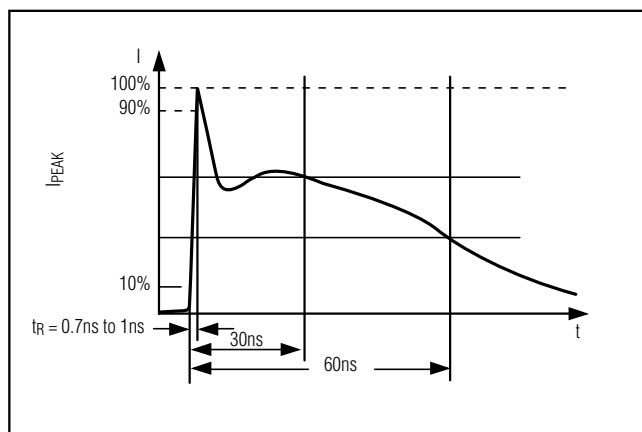


Figure 3. IEC 61000-4-2 ESD Generator Current Waveform

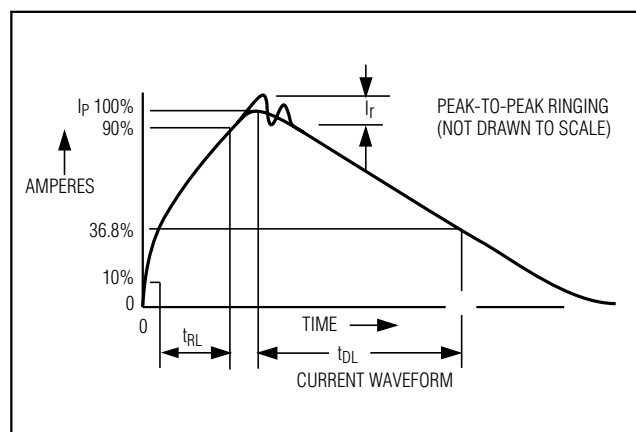


Figure 5. Human Body Model Current Waveform

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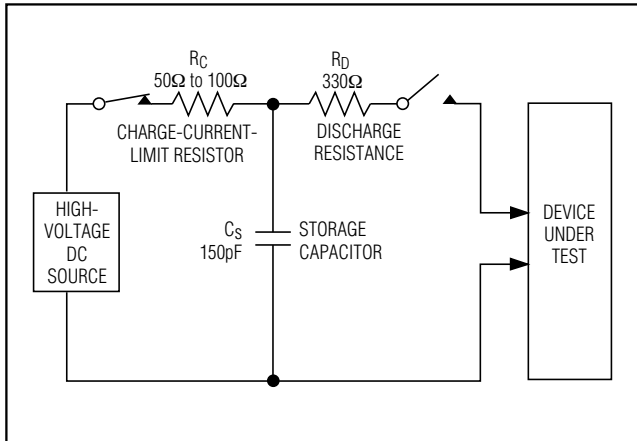


Figure 6. IEC 61000-4-2 ESD Test Model

IEC 61000-4-2

The IEC 61000-4-2 standard covers ESD testing and performance of finished equipment. The MAX13204E/MAX13206E/MAX13208E help users design equipment that meets Level 4 of IEC 61000-4-2.

The main difference between tests done using the Human Body Model and IEC 61000-4-2 is higher peak current in IEC 61000-4-2. Because series resistance is lower in the IEC 61000-4-2 ESD test model (Figure 6), the ESD-withstand voltage measured to this standard is generally lower than that measured using the Human Body Model. Figure 3 shows the current waveform for the $\pm 8\text{kV}$ IEC 61000-4-2 Level 4 ESD Contact Discharge test.

The Air-Gap Discharge test involves approaching the device with a charged probe. The Contact Discharge method connects the probe to the device before the probe is energized.

Layout Recommendations

Proper circuit-board layout is critical to suppress ESD-induced line transients. The MAX13204E/MAX13206E/MAX13208E clamp to $\pm 120\text{V}$; however, with improper layout, the voltage spike at the device is much higher. A lead inductance of 10nH with a 45A current spike at a dv/dt of 1ns results in an **ADDITIONAL** 450V spike on the protected line. It is **essential** that the layout of the PC board follows these guidelines:

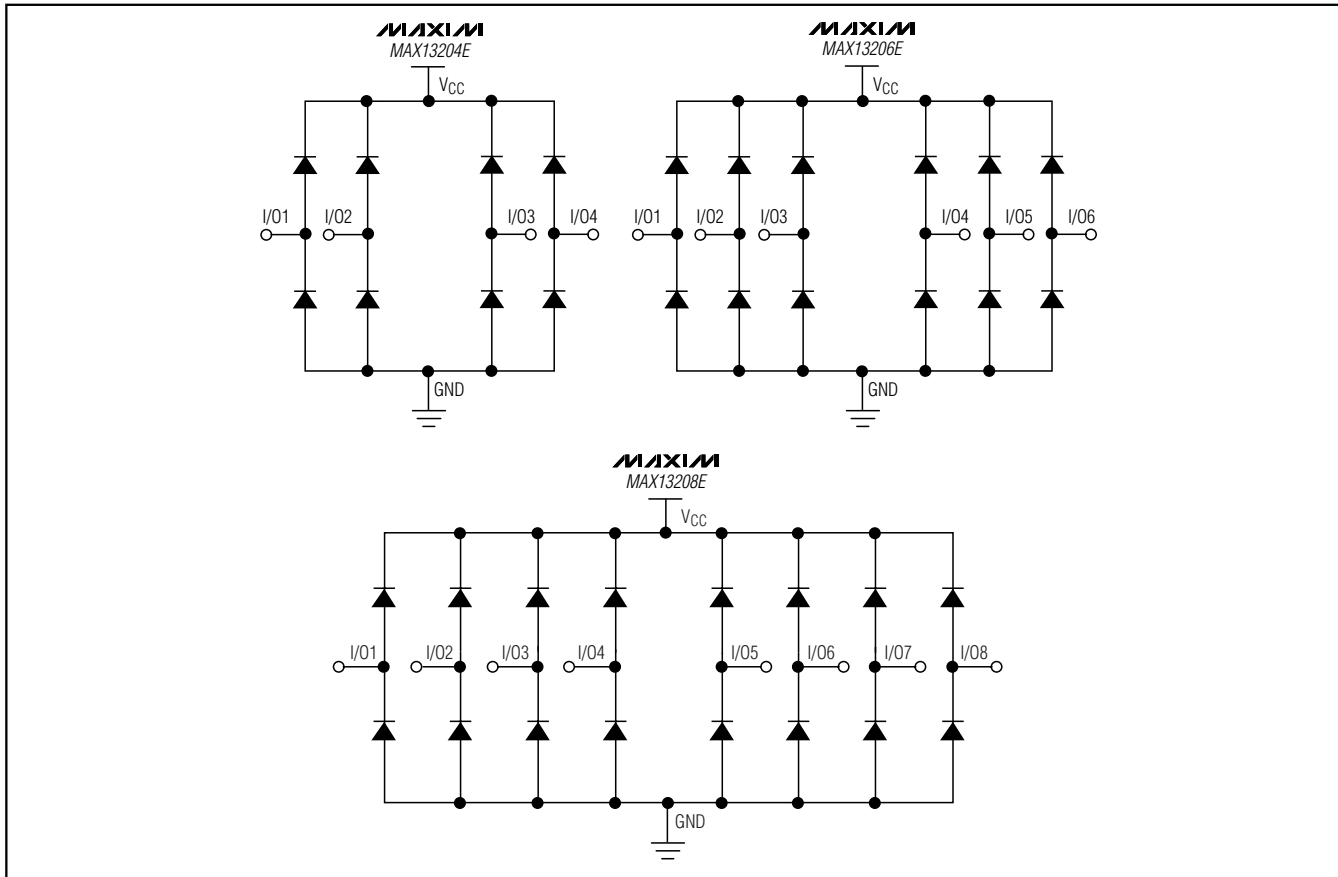
- 1) Minimize trace length between the connector or input terminal, I/O_, and the protected signal line.
- 2) Use separate planes for power and ground to reduce parasitic inductance and to reduce the impedance to the power rails for shunted ESD current.
- 3) Ensure short ESD transient return paths to GND and VCC.
- 4) Minimize conductive power and ground loops.
- 5) Do not place critical signals near the edge of the PC board.
- 6) Bypass VCC to GND with a low-ESR ceramic capacitor as close to VCC and ground terminals as possible.
- 7) Bypass the supply of the protected device to GND with a low-ESR ceramic capacitor as close to the supply pin as possible.

Chip Information

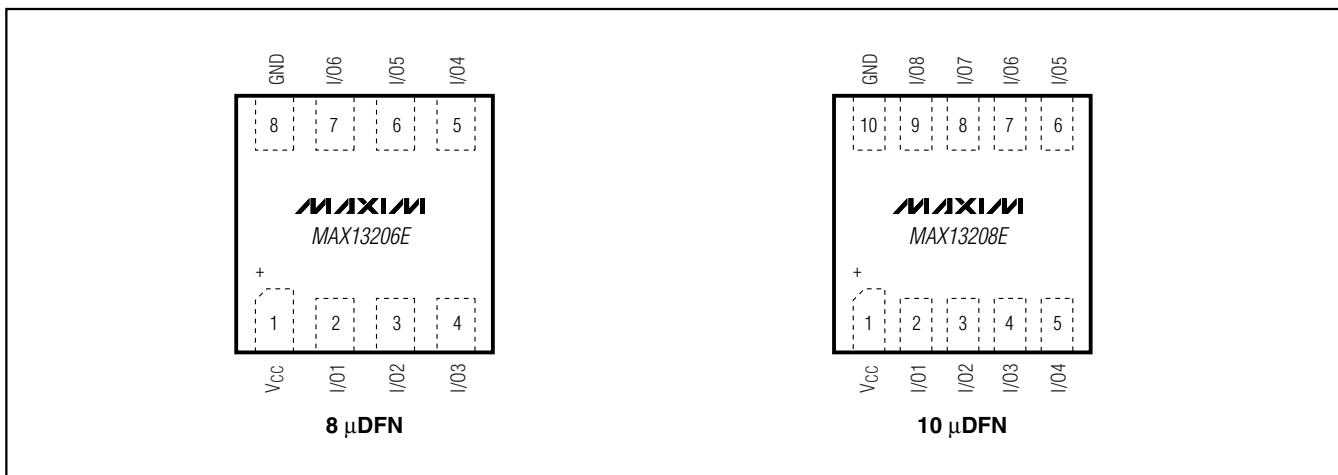
PROCESS: BiCMOS

4-/6-/8-Channel, $\pm 30\text{kV}$ ESD Protectors in μDFN

Functional Diagrams



Pin Configurations (continued)

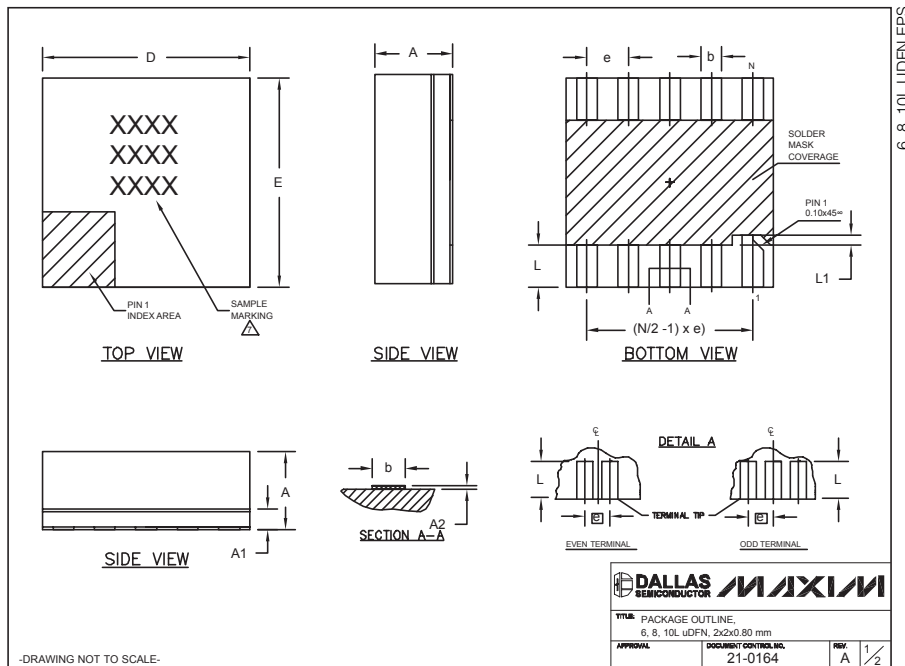


MAX13204E/MAX13206E/MAX13208E

4-/6-/8-Channel, $\pm 30\text{kV}$ ESD Protectors in μDFN

Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information go to www.maxim-integrated.com/packages.)



COMMON DIMENSIONS			
SYMBOL	MIN.	NOM.	MAX.
A	0.70	0.75	0.80
A1	0.15	0.20	0.25
A2	0.020	0.025	0.035
D	1.95	2.00	2.05
E	1.95	2.00	2.05
L	0.30	0.40	0.50
L1	0.10 REF.		

PACKAGE VARIATIONS				
PKG. CODE	N	e	b	(N/2 - 1) x e
L622-1	6	0.65 BSC	0.30±0.05	1.30 REF.
L822-1	8	0.50 BSC	0.25±0.05	1.50 REF.
L1022-1	10	0.40 BSC	0.20±0.03	1.60 REF.

NOTES:

- ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
- COPLANARITY SHALL NOT EXCEED 0.08mm.
- WARPAGE SHALL NOT EXCEED 0.10mm.
- PACKAGE LENGTH/PACKAGE WIDTH ARE CONSIDERED AS SPECIAL CHARACTERISTIC(S).
- "N" IS THE TOTAL NUMBER OF LEADS.
- NUMBER OF LEADS SHOWN ARE FOR REFERENCE ONLY.
- MARKING IS FOR PACKAGE ORIENTATION REFERENCE ONLY.

-DRAWING NOT TO SCALE-

DALLAS SEMICONDUCTOR MAXIM			
TITLE: PACKAGE OUTLINE, 6, 8, 10L UDFN, 2x2x0.80 mm			
APPROVAL	DOCUMENT CONTROL INC.	REV. A	2/2
21-0164			

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